

# IRL3715LPBF-VB Datasheet

## N-Channel 20-V (D-S) MOSFET

### PRODUCT SUMMARY

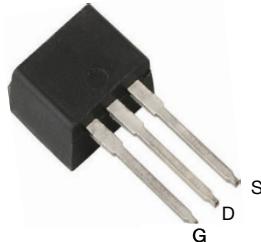
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a, e</sup>	$Q_g$ (Typ)
20	0.0030 at $V_{GS} = 10$ V	95	82 nC
	0.0070 at $V_{GS} = 4.5$ V	70	

### FEATURES

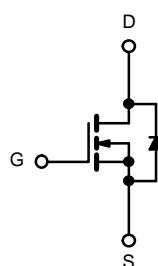
- Trench Power MOSFET
- 100 %  $R_g$  and UIS Tested
- Compliant to RoHS Directive 2011/65/EU



TO-262



Top View



N-Channel MOSFET

### APPLICATIONS

- OR-ing
- Server
- DC/DC

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	95 <sup>a, e</sup>	A
		65 <sup>e</sup>	
		28.8 <sup>b, c</sup>	
		27 <sup>b, c</sup>	
Pulsed Drain Current	$I_{DM}$	300	
Avalanche Current Pulse	$I_{AS}$	36	
Single Pulse Avalanche Energy	$E_{AS}$	104	
Continuous Source-Drain Diode Current	$I_S$	90 <sup>a, e</sup>	A
		3.13 <sup>b, c</sup>	
Maximum Power Dissipation	$P_D$	250 <sup>a</sup>	W
		175	
		3.75 <sup>b, c</sup>	
		2.63 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 175	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	$R_{thJA}$	32	40	°C/W
Maximum Junction-to-Case	$R_{thJC}$	0.5	0.6	

Notes:

- a. Based on  $T_C = 25$  °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t = 10$  sec.
- d. Maximum under steady state conditions is 90 °C/W.
- e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

**SPECIFICATIONS** ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)

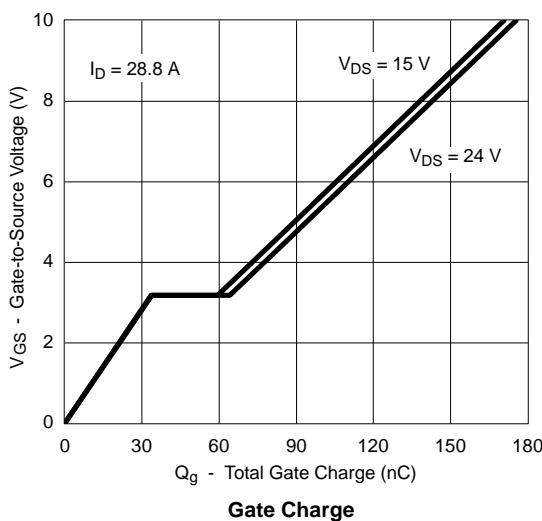
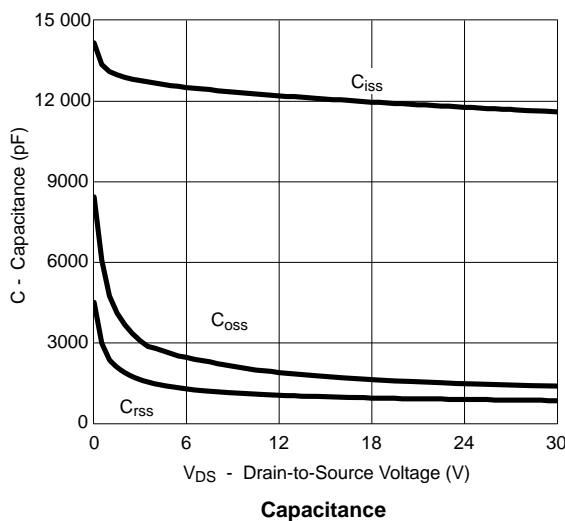
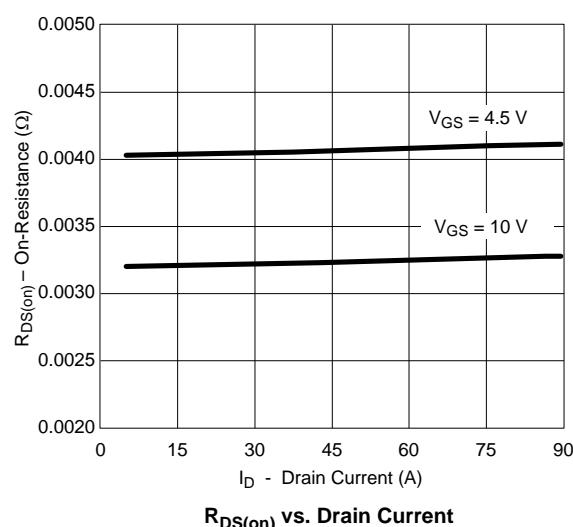
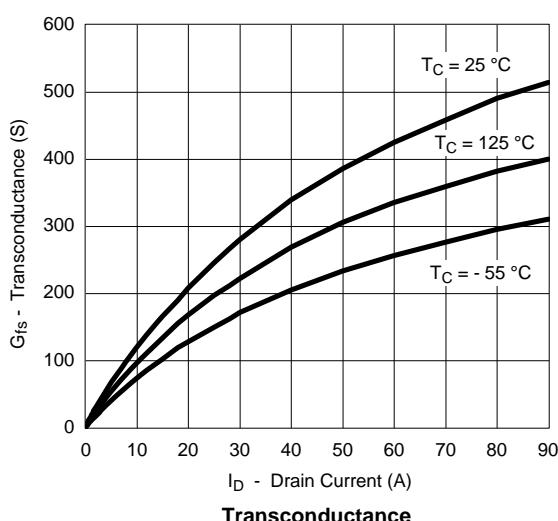
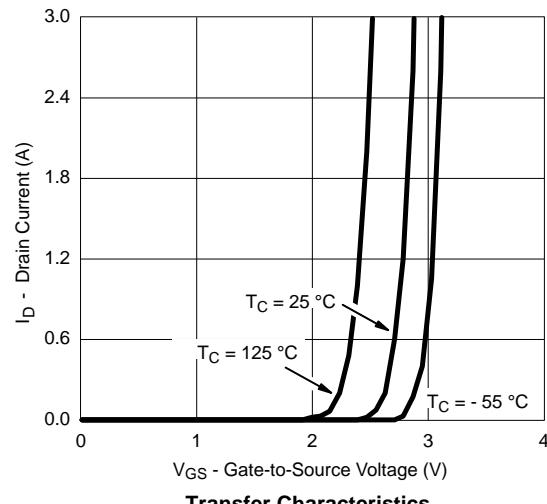
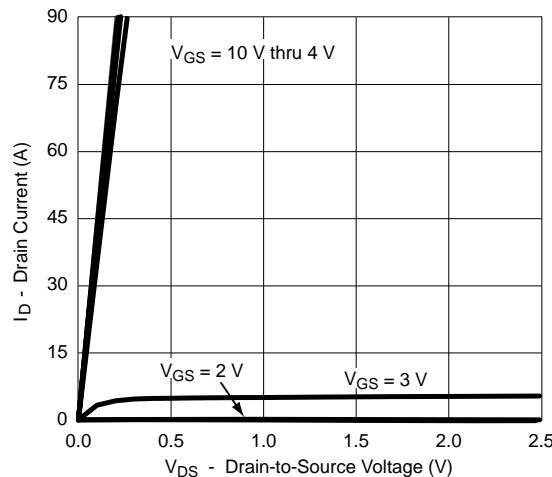
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	20			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		35		mV/°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			- 7.5		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	0.5		2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20 \text{ V}$ , $V_{GS} = 0 \text{ V}$		1		$\mu\text{A}$
		$V_{DS} = 20 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 55^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$ , $V_{GS} = 10 \text{ V}$	90			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$ , $I_D = 20 \text{ A}$		0.0030		$\Omega$
		$V_{GS} = 4.5 \text{ V}$ , $I_D = 20 \text{ A}$		0.0070		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}$ , $I_D = 28.8 \text{ A}$		160		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		4000		pF
Output Capacitance	$C_{oss}$			1725		
Reverse Transfer Capacitance	$C_{rss}$			970		
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 28.8 \text{ A}$		171	257	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}$ , $V_{GS} = 4.5 \text{ V}$ , $I_D = 28.8 \text{ A}$		81.5	123	
Gate-Drain Charge	$Q_{gd}$			34		
Gate Resistance	$R_g$		$f = 1 \text{ MHz}$	29		
Turn-On Delay Time	$t_{d(\text{on})}$			1.4	2.1	$\Omega$
Rise Time	$t_r$	$V_{DD} = 15 \text{ V}$ , $R_L = 0.625 \Omega$ $I_D \cong 24 \text{ A}$ , $V_{GEN} = 10 \text{ V}$ , $R_g = 1 \Omega$		18	27	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			11	17	
Fall Time	$t_f$			70	105	
Turn-On Delay Time	$t_{d(\text{on})}$			10	15	
Rise Time	$t_r$	$V_{DD} = 15 \text{ V}$ , $R_L = 0.67 \Omega$ $I_D \cong 22.5 \text{ A}$ , $V_{GEN} = 4.5 \text{ V}$ , $R_g = 1 \Omega$		55	83	
Turn-Off Delay Time	$t_{d(\text{off})}$			180	270	
Fall Time	$t_f$			55	83	
				12	18	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25^\circ\text{C}$			90	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				90	
Body Diode Voltage	$V_{SD}$	$I_S = 22 \text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $T_J = 25^\circ\text{C}$		52	78	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			70.2	105	nC
Reverse Recovery Fall Time	$t_a$			27		ns
Reverse Recovery Rise Time	$t_b$			25		

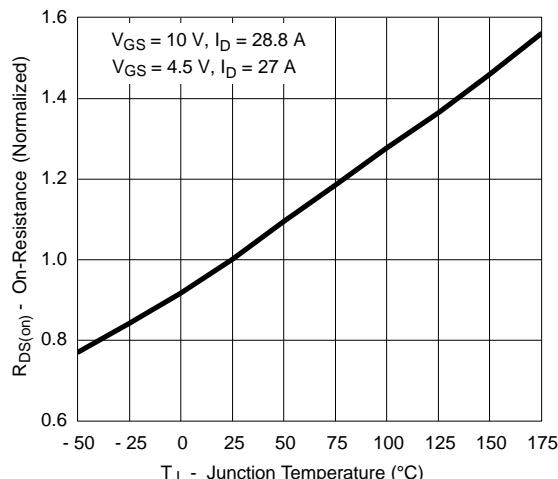
Notes:

a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .

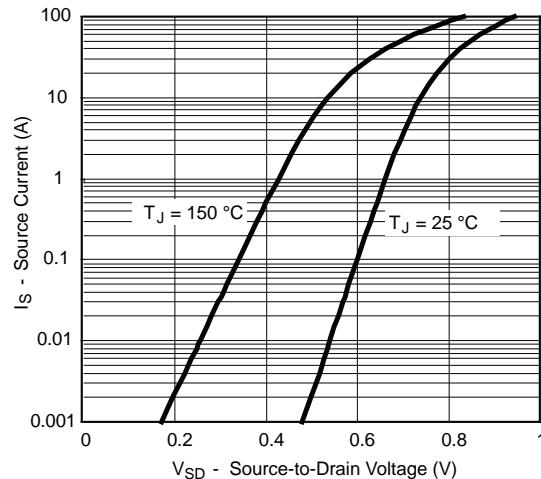
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

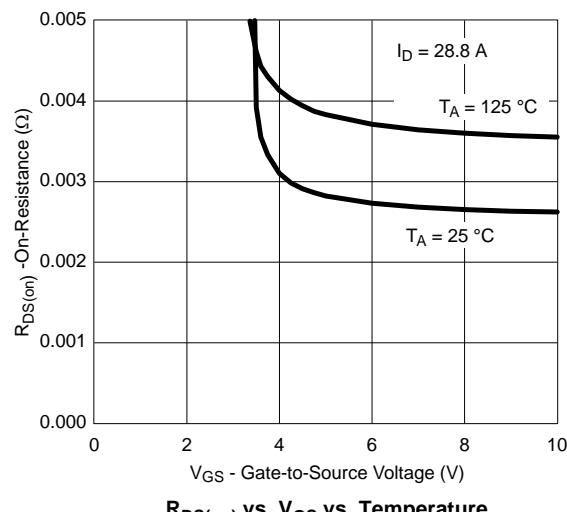
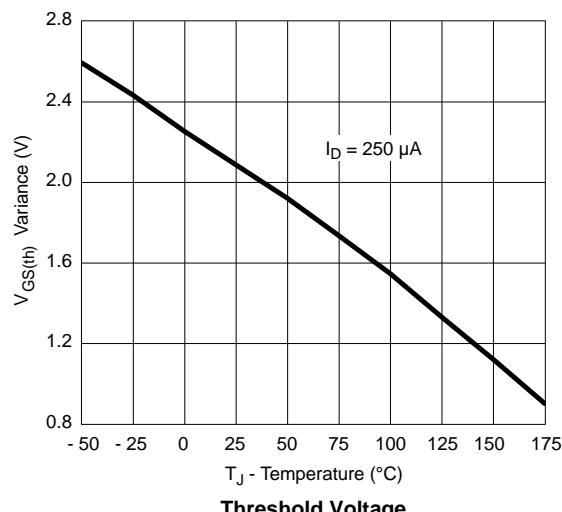
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


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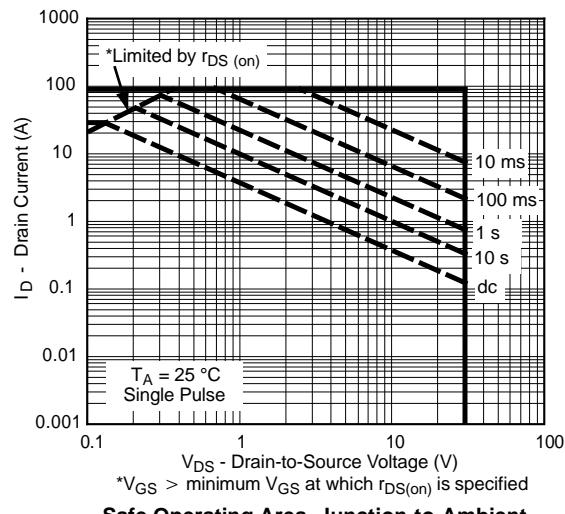
On-Resistance vs. Junction Temperature



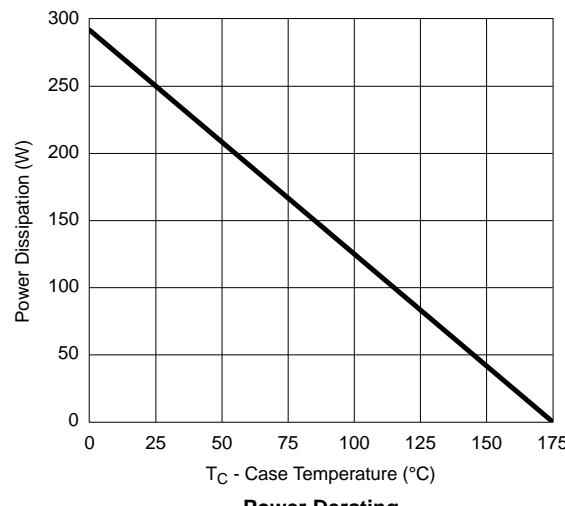
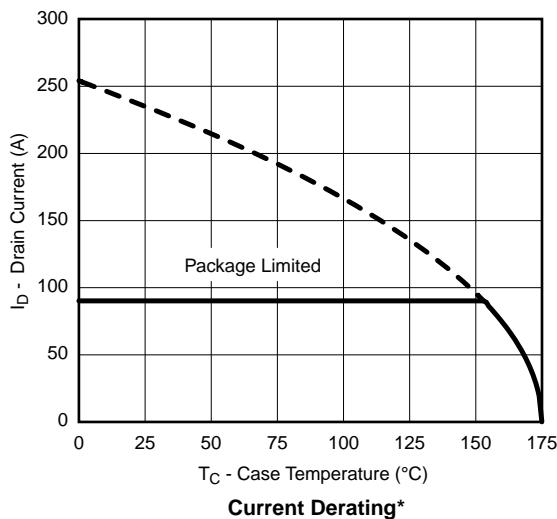
Forward Diode Voltage vs. Temperature

 $R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature

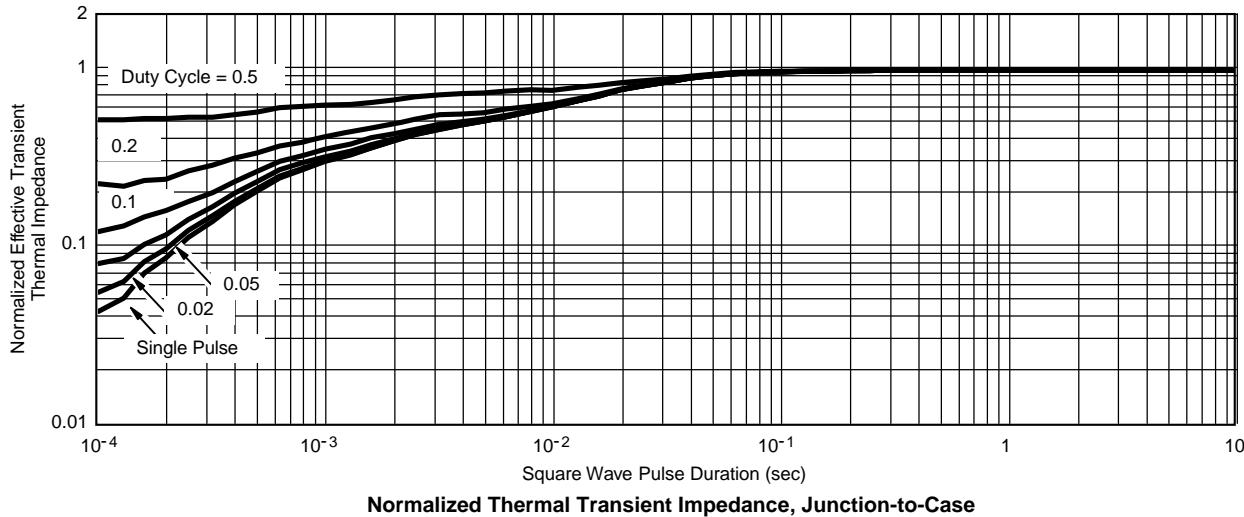
Threshold Voltage



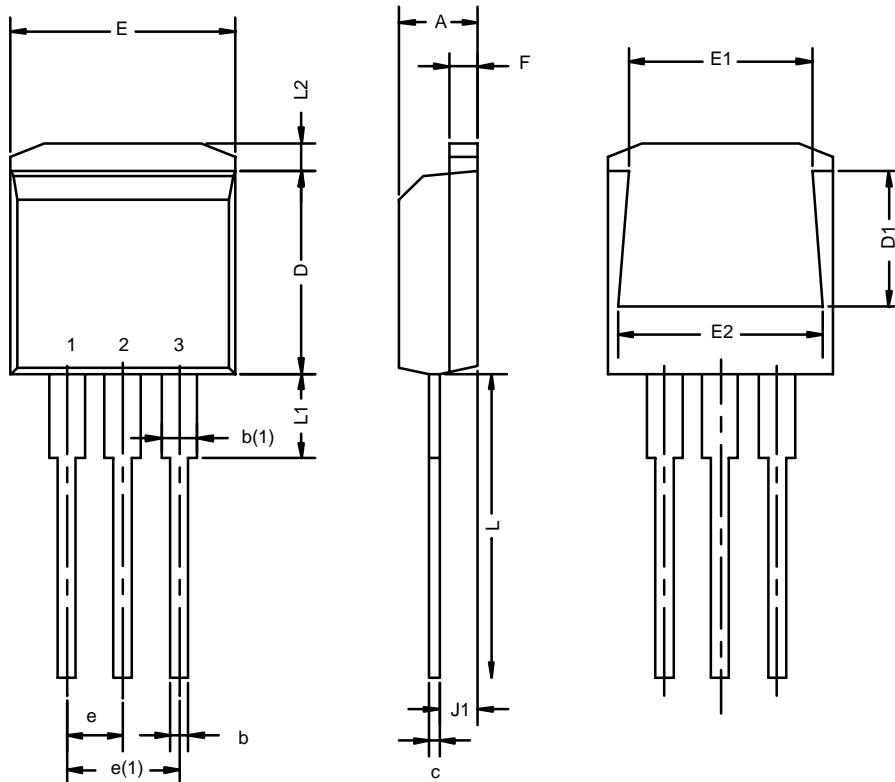
Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


\*The power dissipation  $P_D$  is based on  $T_{J(max)} = 175$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



## TO-262: 3-LEAD



Dim	MILLIMETERS*		INCHES	
	Min	Max	Min	Max
<b>A</b>	4.32	4.70	0.170	0.185
<b>b</b>	0.64	1.00	0.025	0.039
<b>b(1)</b>	1.14	1.40	0.045	0.055
<b>c</b>	0.36	0.50	0.014	0.020
<b>D</b>	8.64	9.65	0.340	0.380
<b>D1</b>	5.59	6.10	0.220	0.240
<b>e</b>	2.41	2.67	0.095	0.105
<b>e(1)</b>	4.95	5.33	0.195	0.210
<b>E</b>	10.03	10.41	0.395	0.410
<b>E1</b>	7.87	8.64	0.310	0.340
<b>E2</b>	9.02	9.53	0.355	0.375
<b>F</b>	1.14	1.40	0.045	0.055
<b>J1</b>	2.41	2.79	0.095	0.110
<b>L</b>	13.08	14.22	0.515	0.560
<b>L1</b>	-	3.81	-	0.150
<b>L2</b>	1.02	1.40	0.040	0.055

\*Use millimeters as the primary measurement

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